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Nanotechnology and Microelectronics: Materials, Processing, Measurement, and Phenomena

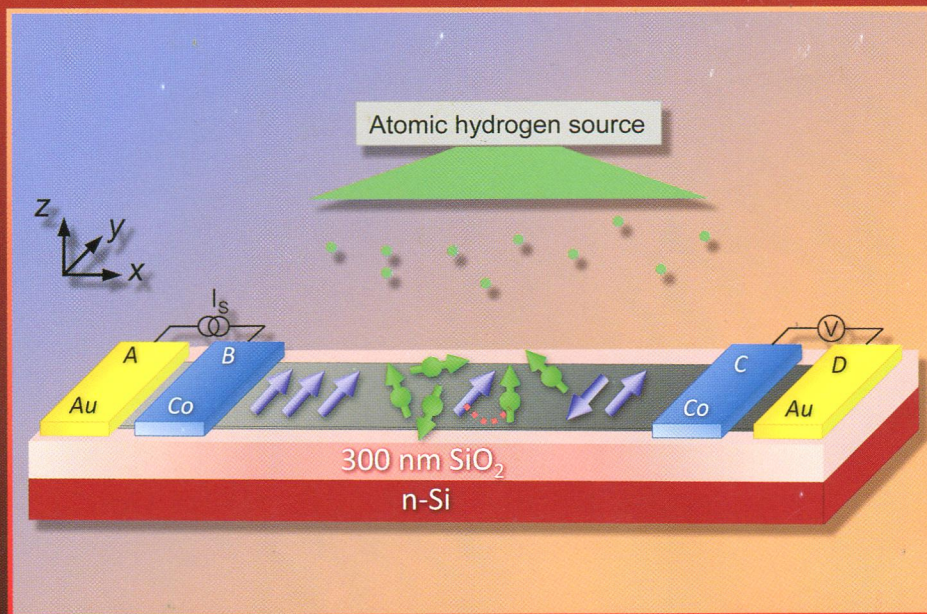
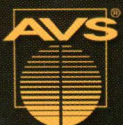


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Nanotechnology and Microelectronics:

Materials, Processing, Measurement, and Phenomena

Second Series
Volume 31, Number 4
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Letters

- Nonvolatile memory characteristics of thin-film transistors using hybrid gate stack composed of solution-processed indium-zinc-silicon oxide active channel and organic ferroelectric gate insulator**
Jun Yong Bak and Sung Min Yoon 040601
- Few layer graphene synthesized by filtered cathodic vacuum arc technique**
Omvir Singh Panwar, Ajay Kumar Kesarwani, Sanjay Rangnath Dhakate, Bhanu Pratap Singh,
Rajib Kumar Rakshit, Atul Bisht, and Sreekumar Chockalingam 040602

Electronic & Optoelectronic Materials, Devices & Processing

- Performance improvement of metal- Al_2O_3 - HfO_2 -oxide-silicon memory devices with band-engineered Hf-aluminate/ SiO_2 tunnel barriers**
Jinho Oh, Heedo Na, Kyumin Lee, Hyunchul Sohn, and Min-Young Heo 041201
- Effect of the $\text{Al}_{0.3}\text{Ga}_{0.7}\text{As}$ interlayer thickness upon the quality of GaAs on a Ge substrate grown by metal-organic chemical vapor deposition**
Senlin Li, Qingqing Chen, Jin Zhang, Huiquan Chen, Wei Xu, Hui Xiong, Zhihao Wu, Yanyan Fang,
Changqing Chen, and Yu Tian 041202

(Continued)

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Structural, morphological, and defect properties of metamorphic $\text{In}_{0.7}\text{Ga}_{0.3}\text{As}/\text{GaAs}_{0.35}\text{Sb}_{0.65}$ p-type tunnel field effect transistor structure grown by molecular beam epitaxy	
Yan Zhu, Mantu K. Hudait, Dheeraj K. Mohata, Bijesh Rajamohanam, Suman Datta, Dmitri Lubyshev, Joel M. Fastenau, and Amy K. Liu	041203
Near-edge x-ray absorption fine structure spectroscopy study of nitrogen incorporation in chemically reduced graphene oxide	
Robert V. Dennis, Brian J. Schultz, Chernoy Jaye, Xi Wang, Daniel A. Fischer, Alexander N. Cartwright, and Sarbajit Banerjee	041204
Improved reliability of Ti/ZrN/Pt resistive switching memory cells using hydrogen postannealing	
Hee-Dong Kim, Min Ju Yun, Seok Man Hong, Ho-Myoung An, and Tae Geun Kim	041205
Growth of high quality ZnO thin films with a homonucleation on sapphire	
Ming Wei, Ryan Casey Boutwell, Nikolai Faleev, Andrei Osinsky, and Winston V. Schoenfeld	041206

Energy Conversion and Storage Devices

Thermoelectric properties of single crystal $\text{Sc}_{1-x}\text{Er}_x\text{As}:\text{InGaAs}$ nanocomposites	
Rachel Koltun, Jacqueline L. Hall, Thomas E. Mates, John E. Bowers, Brian D. Schultz, and Christopher J. Palmström	041401

Lithography

High precision dynamic alignment and gap control for optical near-field nanolithography	
Xiaolei Wen, Luis M. Traverso, Pornsak Srisungsithisunti, Xianfan Xu, and Euclid E. Moon	041601
Focused ion beam induced Ga-contamination—An obstacle for UV-nanoimprint stamp repair?	
Simon Waid, Heinz D. Wanzenboeck, Marco Gavagnin, Ruppert Langegger, Michael Muehlberger, and Emmerich Bertagnolli	041602
Influence of shield roughness on Mo/Si defect density for extreme ultraviolet lithography mask blanks	
Junichi Kageyama, Mamoru Yoshimoto, Akifumi Matsuda, Vibhu Jindal, Patrick Kearney, and Frank Goodwin ...	041603
Method of predicting resist sensitivity for 6.x nm extreme ultraviolet lithography	
Tomoko Gowa Oyama, Akihiro Oshima, Masakazu Washio, and Seiichi Tagawa	041604
Level-set-based inverse lithography for mask synthesis using the conjugate gradient and an optimal time step	
Wen Lv, Shiyuan Liu, Qi Xia, Xiaofei Wu, Yijiang Shen, and Edmund Y. Lam	041605

Nanometer Science & Technology

Effect of lateral tip stiffness on atomic-resolution force field spectroscopy	
Berkin Uluutku and Mehmet Z. Baykara	041801
Atom probe tomography of AlInN/GaN HEMT structures	
Nabil Dawahre, Gang Shen, Steven N. Renfrow, Seongsin M. Kim, and Patrick Kung	041802
Growth, doping, and characterization of ZnO nanowire arrays	
Gang Shen, Nabil Dawahre, Joseph Waters, Seongsin M. Kim, and Patrick Kung	041803
Boron nitride growth on metal foil using solid sources	
Satoru Suzuki, Roger Molto Pallares, Carlo M. Orofeo, and Hiroki Hibino	041804
Optimization of electron beam induced deposition process for the fabrication of diode-like Pt/SiO₂/W devices	
Antonietta Taurino, Isabella Farella, Adriano Cola, Mauro Lomascolo, Fabio Quaranta, and Massimo Catalano ..	041805
Fabrication of high-density Si and Si_xGe_{1-x} nanowire arrays based on the single step plasma etching process	
Mickaël Martin, Sebastien Avertin, Thierry Chevolleau, Florian Dhalluin, Maelig Ollivier, Thierry Baron, Olivier Joubert, and Jean Michel Hartmann	041806

(Continued)

Reducing hole-size variation and defect ratio after pattern transfer by using self-assembled polymer with spherical structure Taku Iwase, Masaru Kurihara, Yoshiyuki Hirayama, Nobuyuki Negishi, Teruaki Hayakawa, Yasuhiko Tada, and Hiroshi Yoshida	041807
Visualizing graphene edges using tip-enhanced Raman spectroscopy Weitao Su and Debdulal Roy	041808

MEMS & NEMS

Micromirrors connected in series for low voltage operation in vacuum Seibou Kotani, Hoang Manh Chu, Takashi Sasaki, and Kazuhiro Hane	042001
---	--------

Microelectronic & Nanoelectronic Devices

Feature profile evolution during shallow trench isolation etching in chlorine-based plasmas. III. The effect of oxygen addition Cheng-che Hsu, Nathan Marchack, Ryan M. Martin, Calvin Pham, John Hoang, and Jane P. Chang	042201
Impact of proton irradiation on dc performance of AlGaIn/GaN high electron mobility transistors Lu Liu, Camilo Velez Cuervo, Yuyin Xi, Fan Ren, Stephen J. Pearton, Hong-Yeol Kim, Jihyun Kim, and Ivan I. Kravchenko	042202
Stability of deflected-beam metal-insulator-metal tunneling cathodes under high acceleration voltage Mutsumi Suzuki and Toshiaki Kusunoki	042203
Hysteresis in experimental I-V curves of electron hop funnels Tyler Rowe, Marcus Pearlman, and Jim Browning	042204

Spintronics and Magnetic Devices

Structural and magnetic properties of NiAs-type FeSe and related alloy layers Guibin Song, Hiroaki Matsui, Hisazumi Akai, and Hitoshi Tabata	042801
--	--------

Shop Notes

Etch-stop method for reliably fabricating sharp yet mechanically stable scanning tunneling microscope tips Gobind Basnet, James Kevin Schoelz, Peng Xu, Steven D. Barber, Matthew L. Ackerman, and Paul M. Thibado	043201
Optimization of an electron beam lithography instrument for fast, large area writing at 10 kV acceleration voltage Martin M. Greve and Bodil Holst	043202

Perspectives

Evolution of Physics and Chemistry of Surfaces and Interfaces: A Perspective of the Last 40 Years David K. Ferry	048501
--	--------

40TH CONFERENCE ON THE PHYSICS AND CHEMISTRY OF SEMICONDUCTOR INTERFACES (40TH PCSI 2013)

Preface	i
Atomic-scale movement induced in nanoridges by scanning tunneling microscopy on epitaxial graphene grown on 4H-SiC(0001) Peng Xu, Steven D. Barber, J. Kevin Schoelz, Matthew L. Ackerman, Dejun Qi, Paul M. Thibado, Virginia D. Wheeler, Luke O. Nyakiti, Rachael L. Myers-Ward, Charles R. Eddy, Jr., and D. Kurt Gaskill	04D101

(Continued)

Tuning the electronic states of individual Co acceptors in GaAs Anne L. Benjamin, Donghun Lee, and Jay A. Gupta.....	04D102
Role of bias voltage and tunneling current in the perpendicular displacements of freestanding graphene via scanning tunneling microscopy Peng Xu, Steven D. Barber, Matthew L. Ackerman, James Kevin Schoelz, and Paul M. Thibado	04D103
Ballistic phonon thermal conductance in graphene nanoribbons Hiroki Tomita and Jun Nakamura	04D104
Integrating MBE materials with graphene to induce novel spin-based phenomena Adrian G. Swartz, Kathleen M. McCreary, Wei Han, Jared J. I. Wong, Patrick M. Odenthal, Hua Wen, Jen-Ru Chen, Roland K. Kawakami, Yufeng Hao, Rodney S. Ruoff, and Jaroslav Fabian	04D105
Epitaxial growth and surface studies of the Half Heusler compound NiTiSn (001) Jason K. Kawasaki, Thomas Neulinger, Rainer Timm, Martin Hjort, Alexei A. Zakharov, Anders Mikkelsen, Brian D. Schultz, and Chris J. Palmstrøm	04D106
Combined <i>in-situ</i> photoemission spectroscopy and density functional theory of the Sr Zintl template for oxide heteroepitaxy on Si(001) Hosung Seo, Miri Choi, Agham B. Posadas, Richard C. Hatch, and Alexander A. Demkov	04D107
Thermoelectric properties of a chain of coupled quantum dots embedded in a nanowire David M.-T. Kuo and Yia-Chung Chang	04D108
CdZnS quantum dots formed by the Langmuir–Blodgett technique Alexander G. Milekhin, Nikolay A. Yeryukov, Larisa L. Sveshnikova, Tatyana A. Duda, Dmitry Yu. Protasov, Anton K. Gutakovskii, Stepan A. Batsanov, Nikolay V. Surovtsev, Sergey V. Adichtchev, Cameliu Himcinschi, Volodymir Dzhagan, Francisc Haidu, and Dietrich R. T. Zahn.....	04D109
Optical properties of solution-processed LaAlO₃/Si films using spectroscopic ellipsometry Tae Jung Kim, Soo Min Hwang, Jae Jin Yoon, Soon Yong Hwang, Han Gyeol Park, Jun Young Kim, Junho Choi, Young Dong Kim, Seung Muk Lee, and Jinho Joo	04D110
Characterization of Al₂O₃/GaAs interfaces and thin films prepared by atomic layer deposition Ram Ekwil Sah, Christoph Tegenkamp, Martina Baeumler, Frank Bernhardt, Rachid Driad, Michael Mikulla, and Oliver Ambacher	04D111
Interfacial polymer ferroelectric dipole induced electric field effect on the photovoltaic performance of organic solar cells Alok C. Rastogi	04D112
Resonant coupling for contactless measurement of carrier lifetime Richard K. Ahrenkiel	04D113
Temperature dependent growth morphologies of parahexaphenyl on SiO₂ supported exfoliated graphene Markus Kratzer, Stefan Klima, Christian Teichert, Borislav Vasić, Aleksandar Matković, Uroš Ralević, and Radoš Gajić	04D114
CUMULATIVE AUTHOR INDEX	A13

On The Cover: *Adrian G. Swartz, Kathleen M. McCreary, Wei Han, Jared J. I. Wong, Patrick M. Odenthal, Hua Wen, Jen-Ru Chen, and Roland K. Kawakami, JVST B, 31(4), p. 04D105-4 (2013). Cover shows hydrogen-induced magnetic moments on graphene detected by spin transport measurements.*